

WHAT IS CLAIMED IS:

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1. A group III nitride compound semiconductor light-emitting device comprising:

a light-emitting layer of a multilayer quantum well structure composed of alternately laminated well layers and barrier layers; and

an n-type clad layer being in contact with said light-emitting layer,

wherein said n-type clad layer is made thicker than each of said barrier layers.

2. A group III nitride compound semiconductor light-emitting device according to claim 1, wherein a thickness of said n-type clad layer is not smaller than 100Å.

3. A group III nitride compound semiconductor light-emitting device according to claim 1, wherein a thickness of said n-type clad layer is not larger than 500Å.

4. A group III nitride compound semiconductor light-emitting device according to claim 1, further comprising an intermediate layer which is provided so as to be in contact with a face of said n-type clad layer opposite to said light-emitting layer.

5. A group III nitride compound semiconductor light-emitting device according to claim 4, wherein said intermediate layer is made of $\text{In}_x\text{Ga}_{1-x}\text{N}$ ($0 < x < 1$).

6. A group III nitride compound semiconductor light-emitting device according to claim 4, wherein said intermediate layer is made of $\text{In}_x\text{Ga}_{1-x}\text{N}$ ($0.01 \leq x \leq 0.05$).

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